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Int. Cl.

H03F 3/24

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(2006.01)

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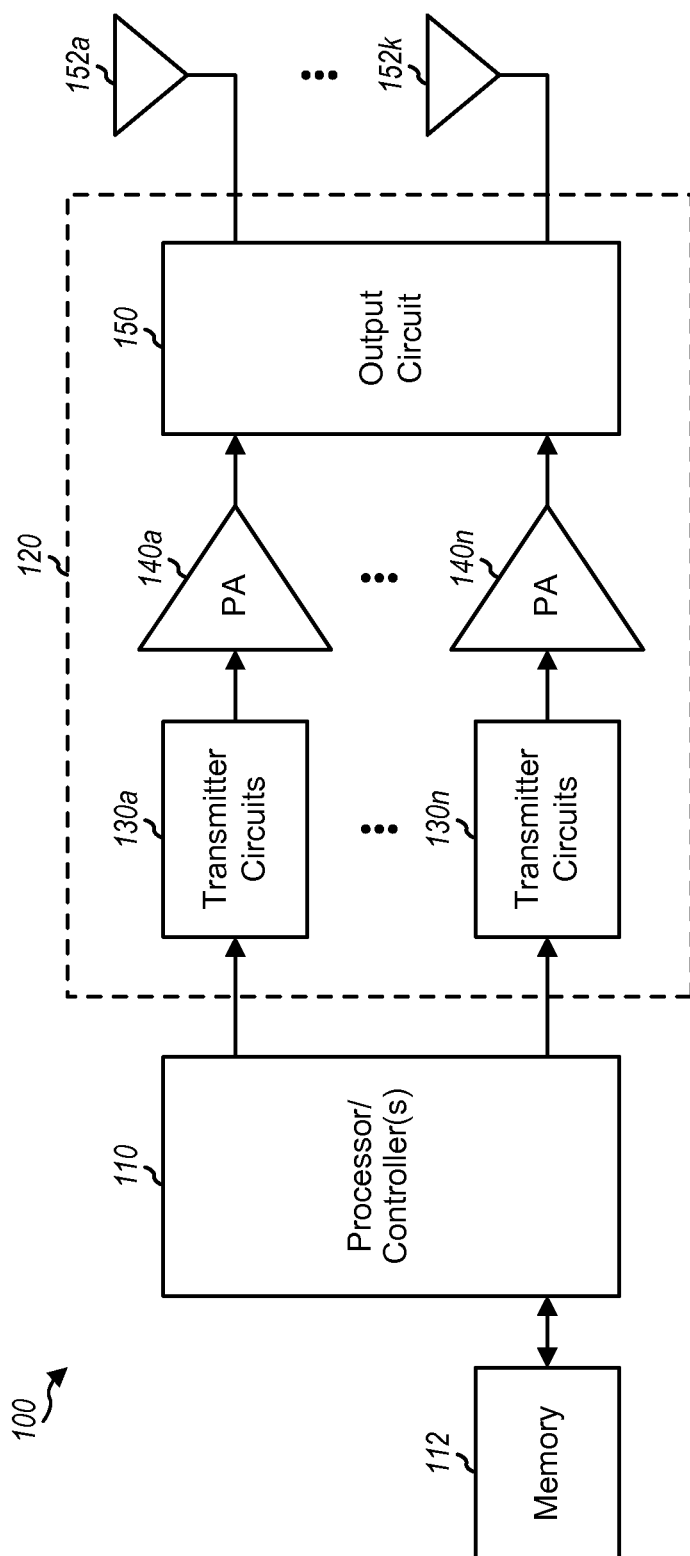
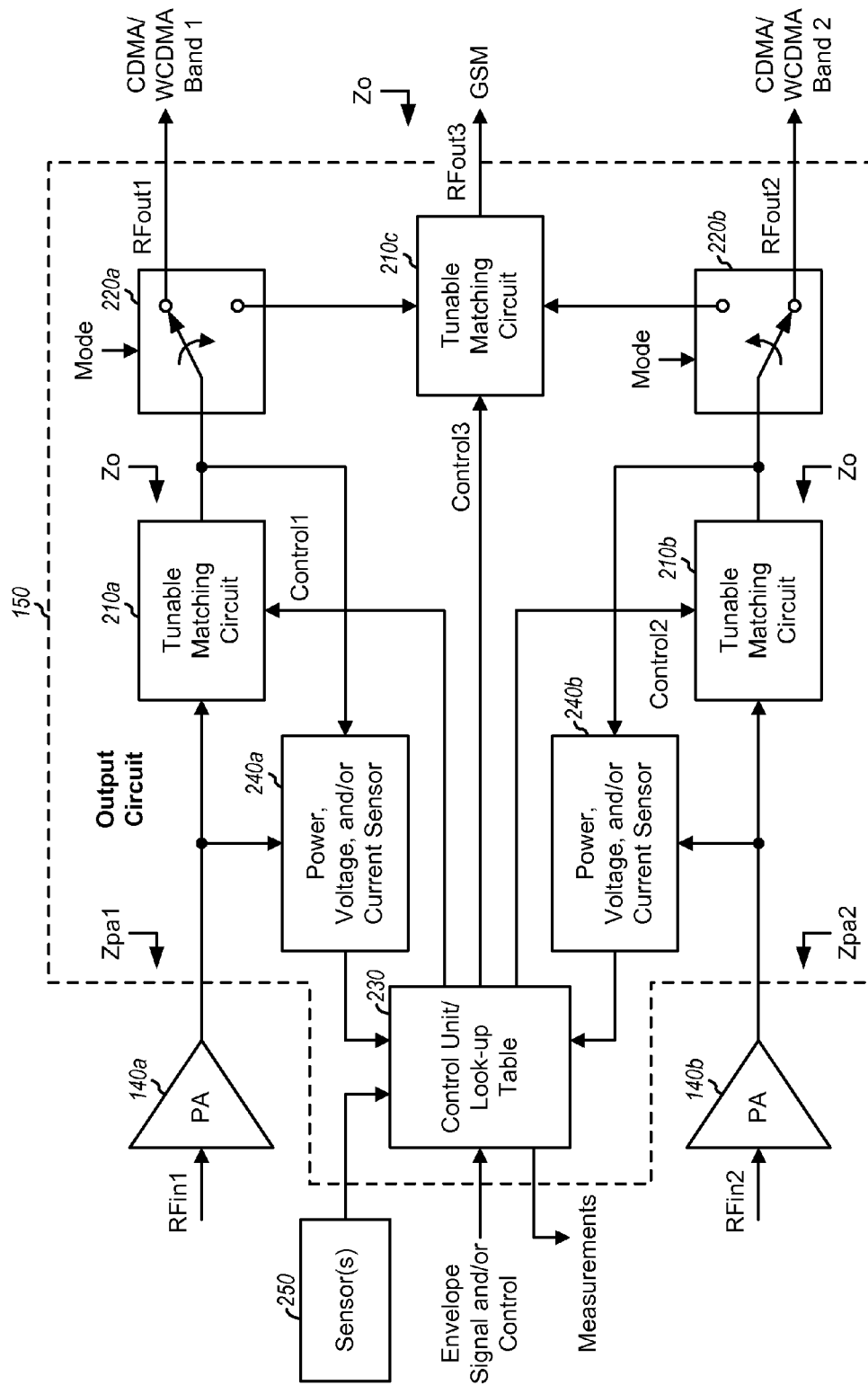


FIG. 1



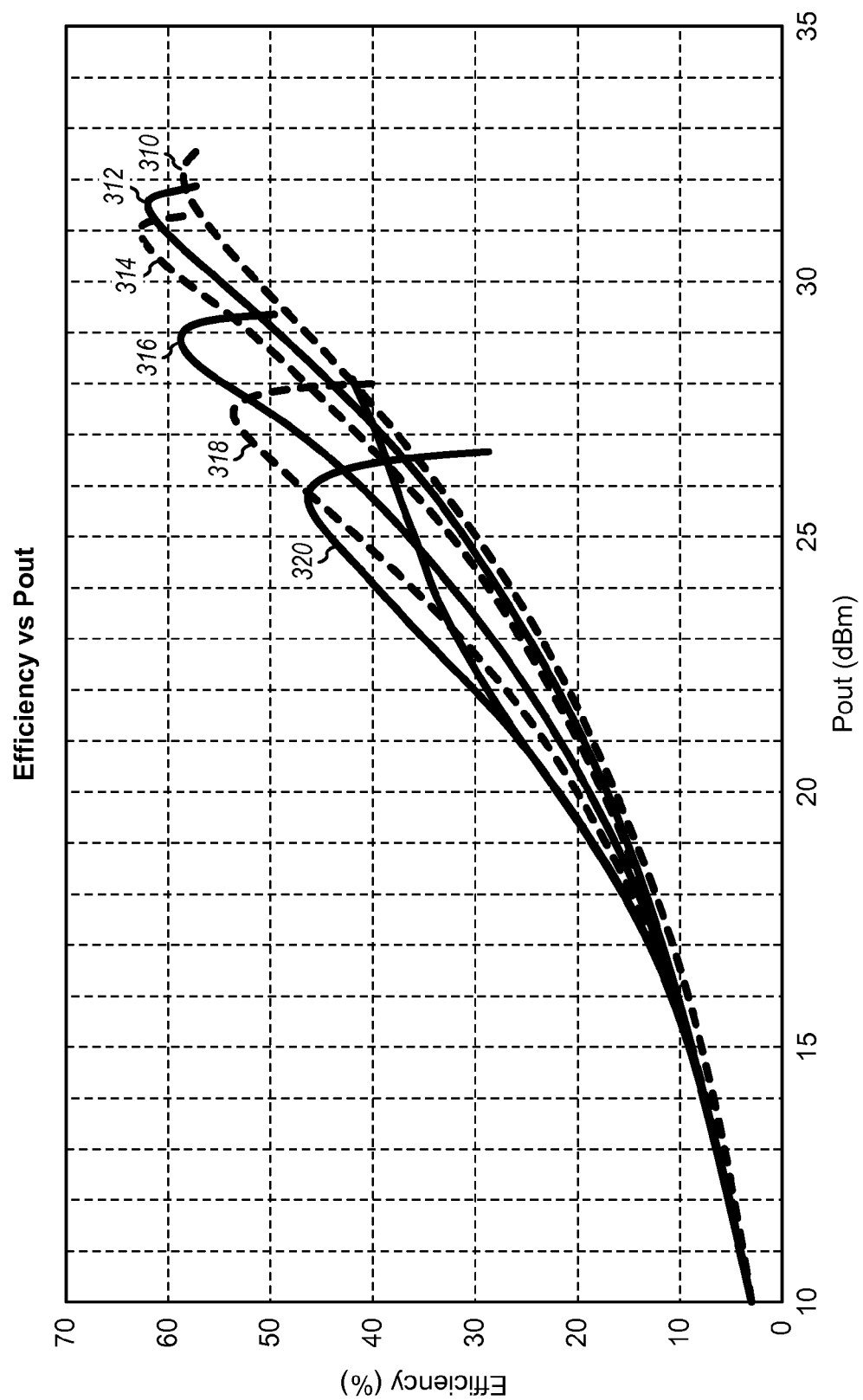


FIG. 3

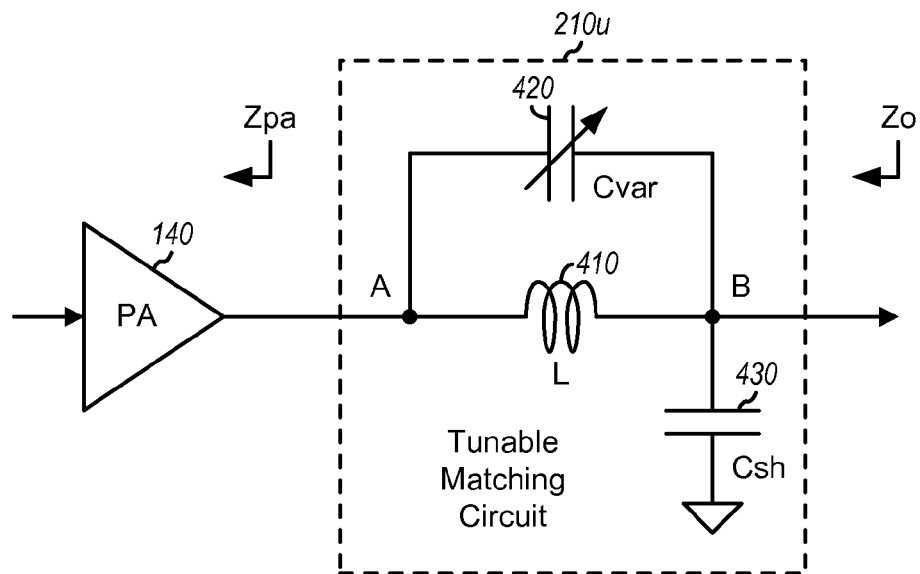


FIG. 4A

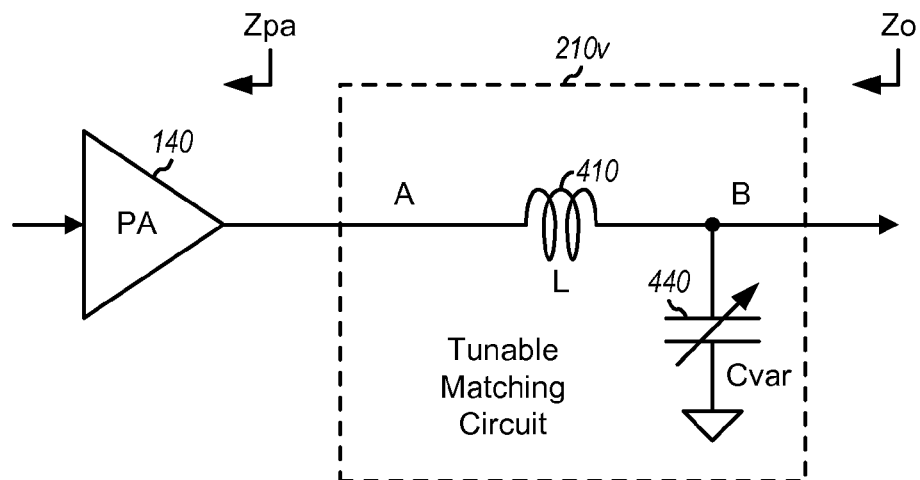


FIG. 5A

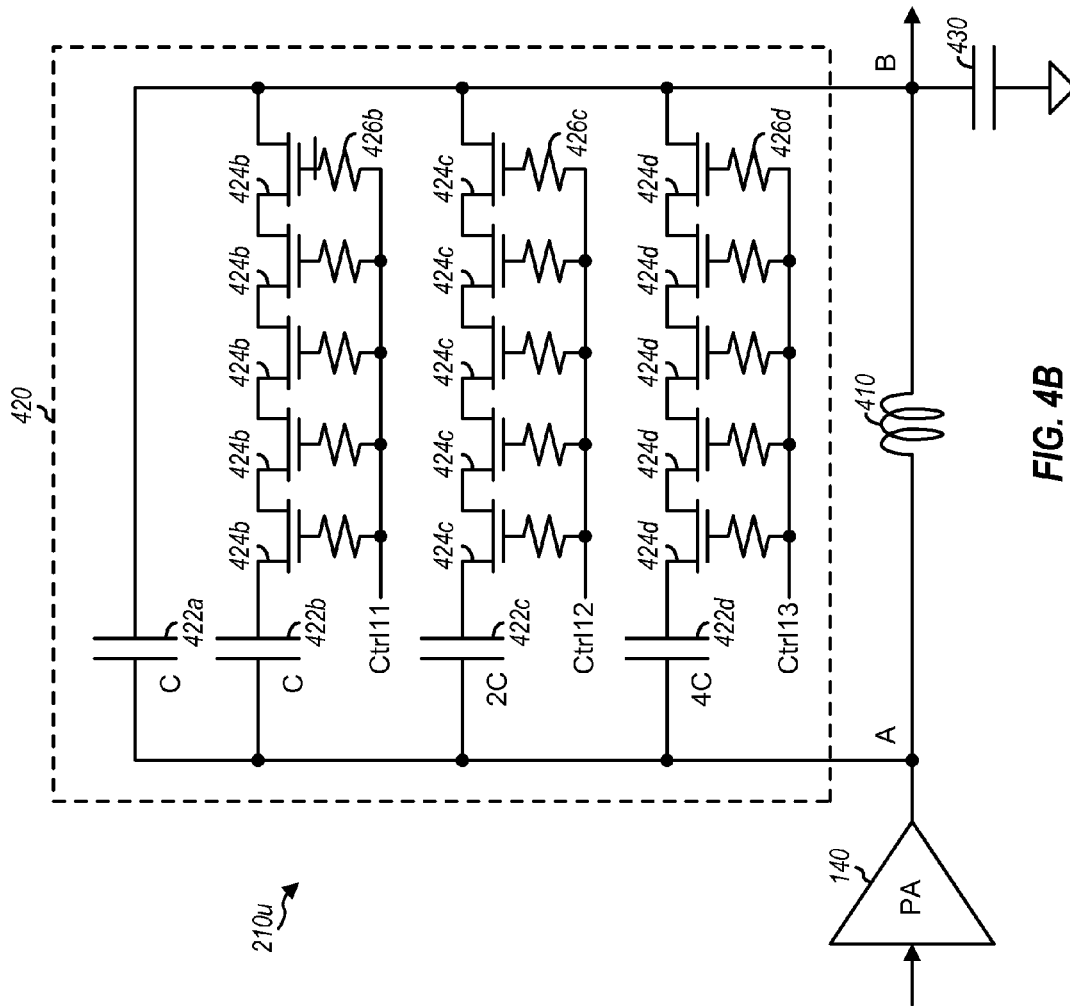


FIG. 4B

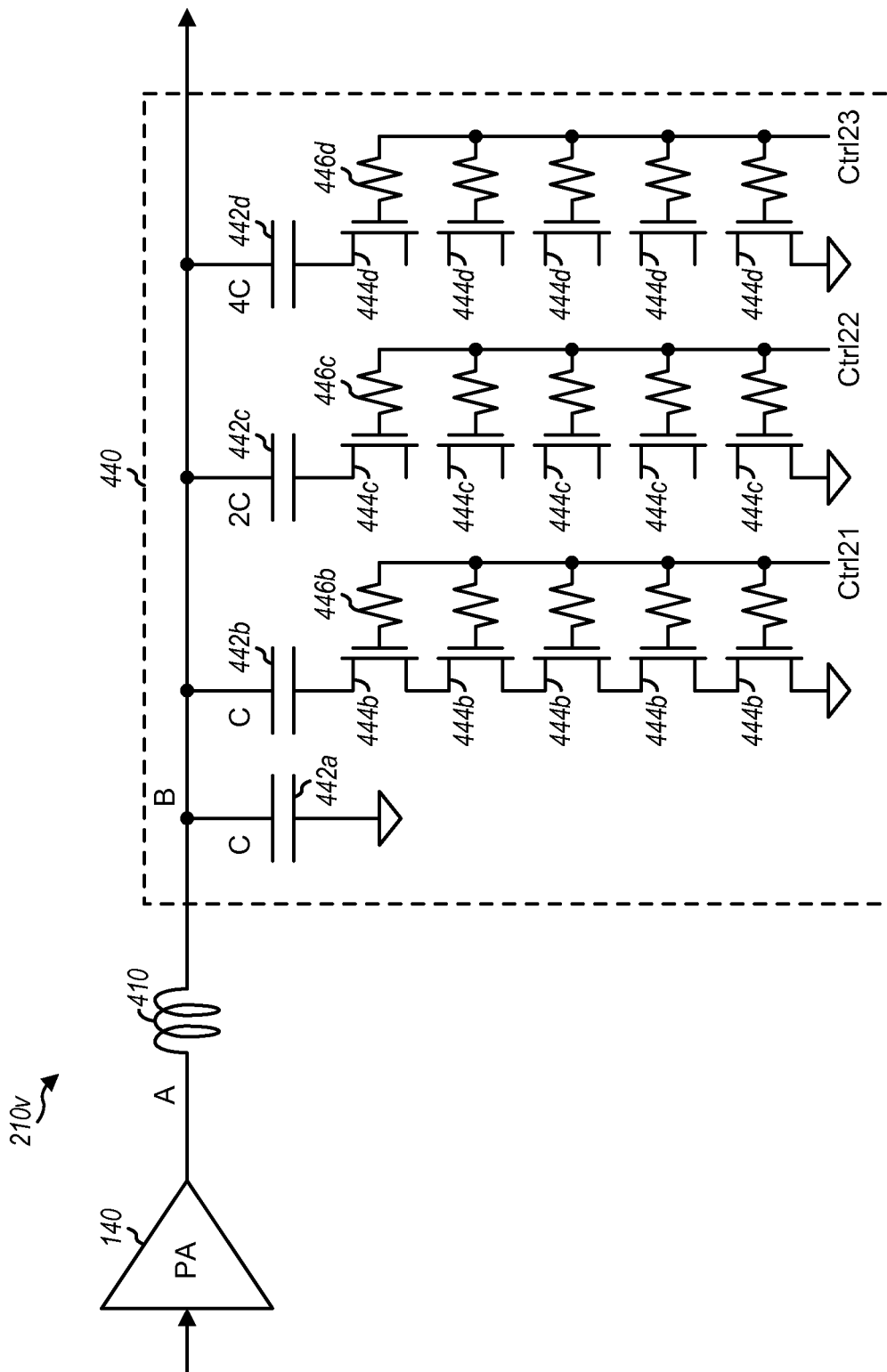


FIG. 5B

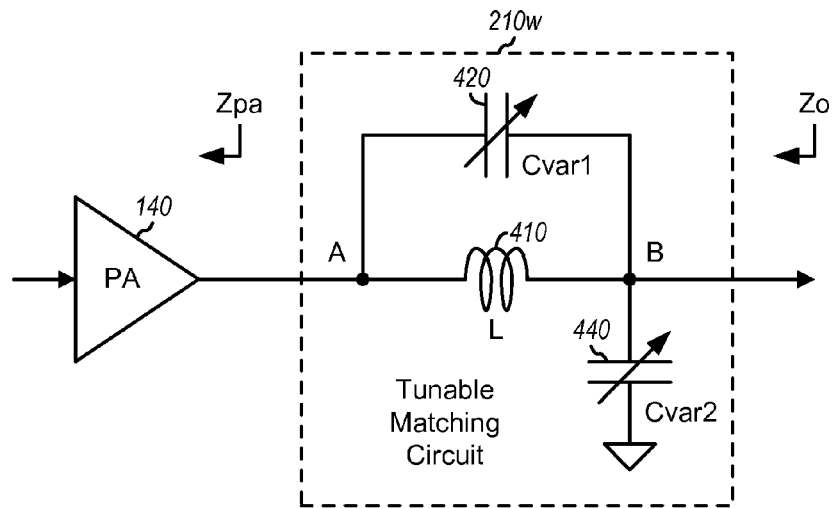


FIG. 6A

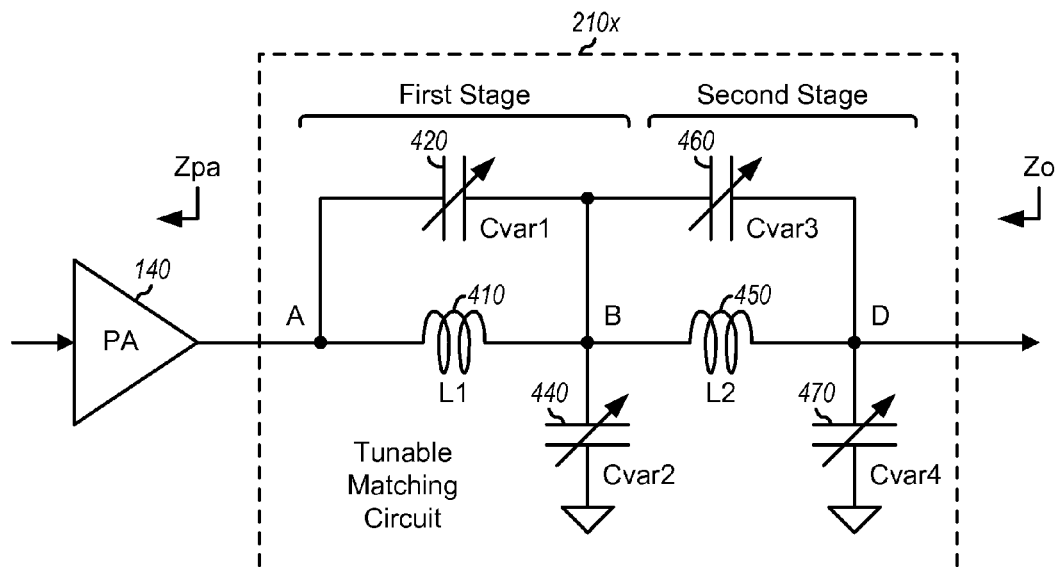


FIG. 7A

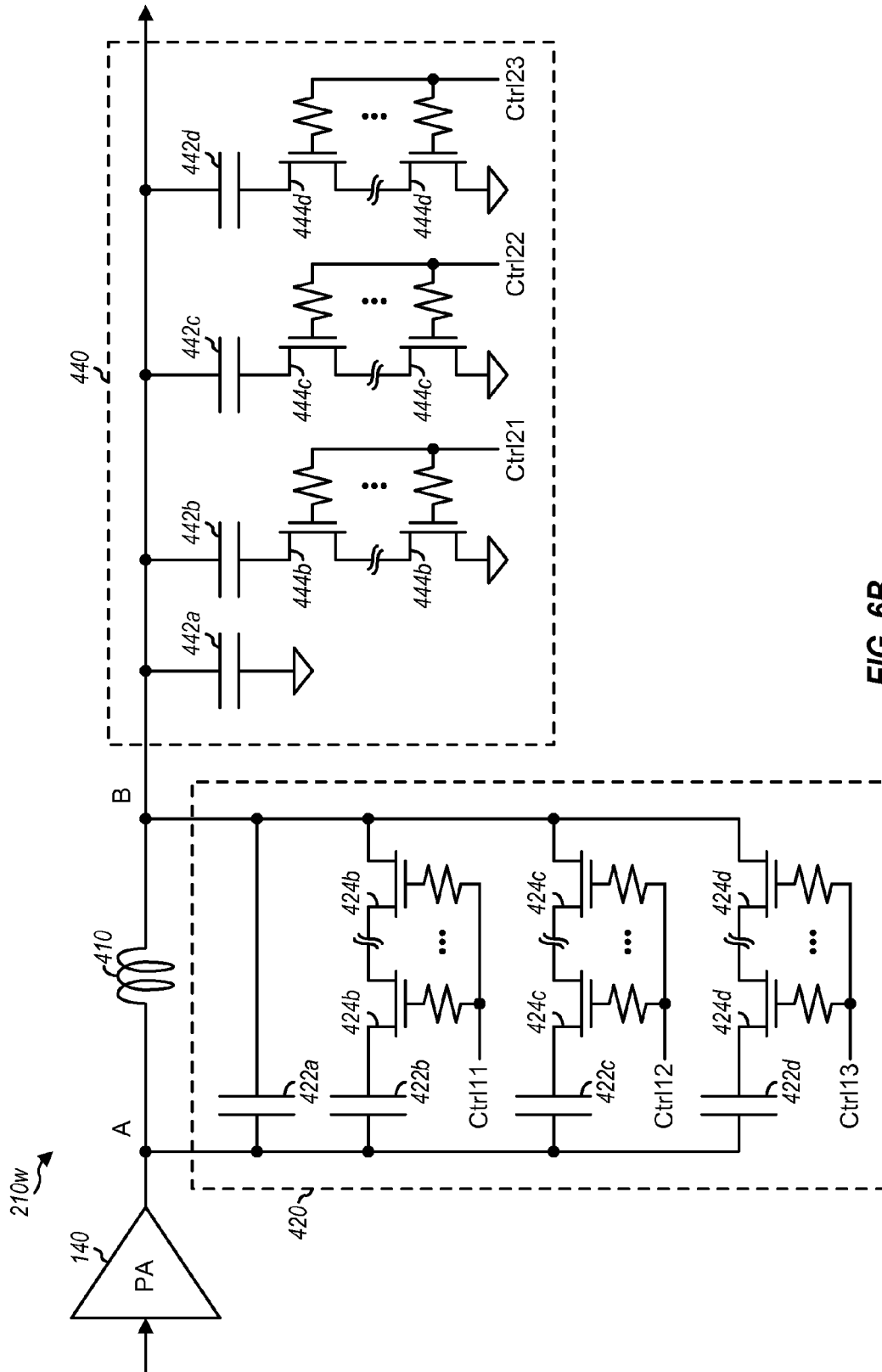
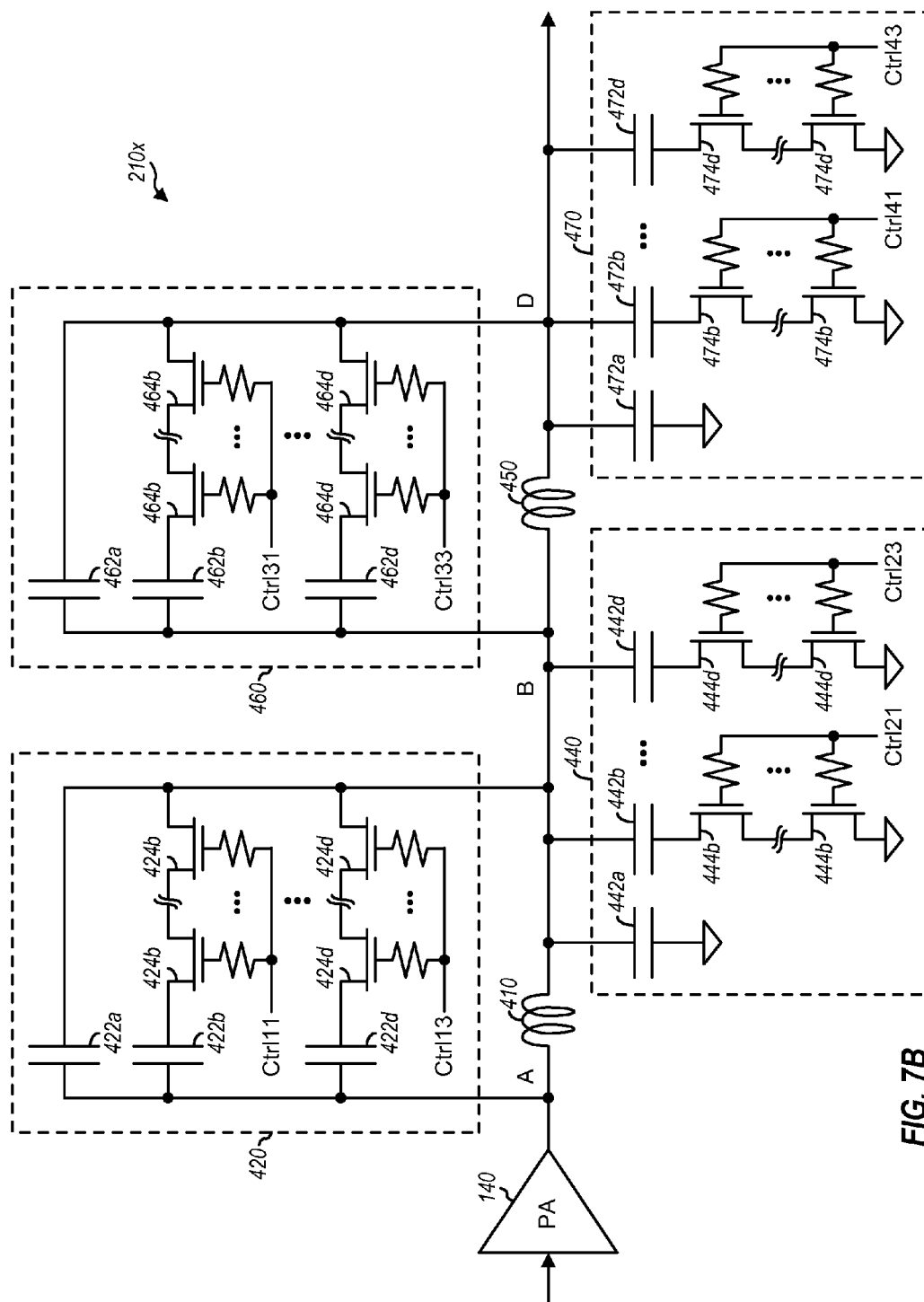


FIG. 6B



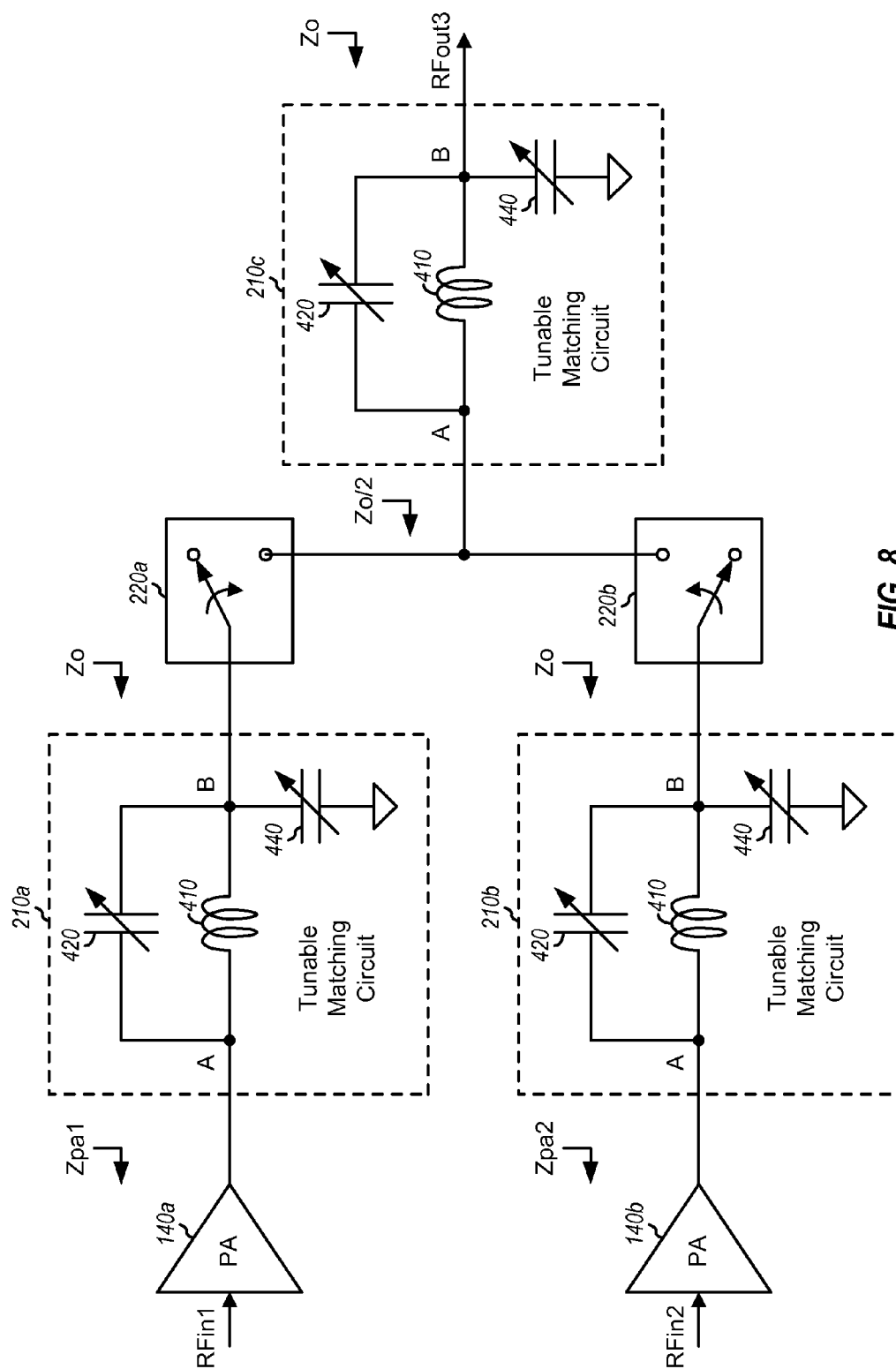
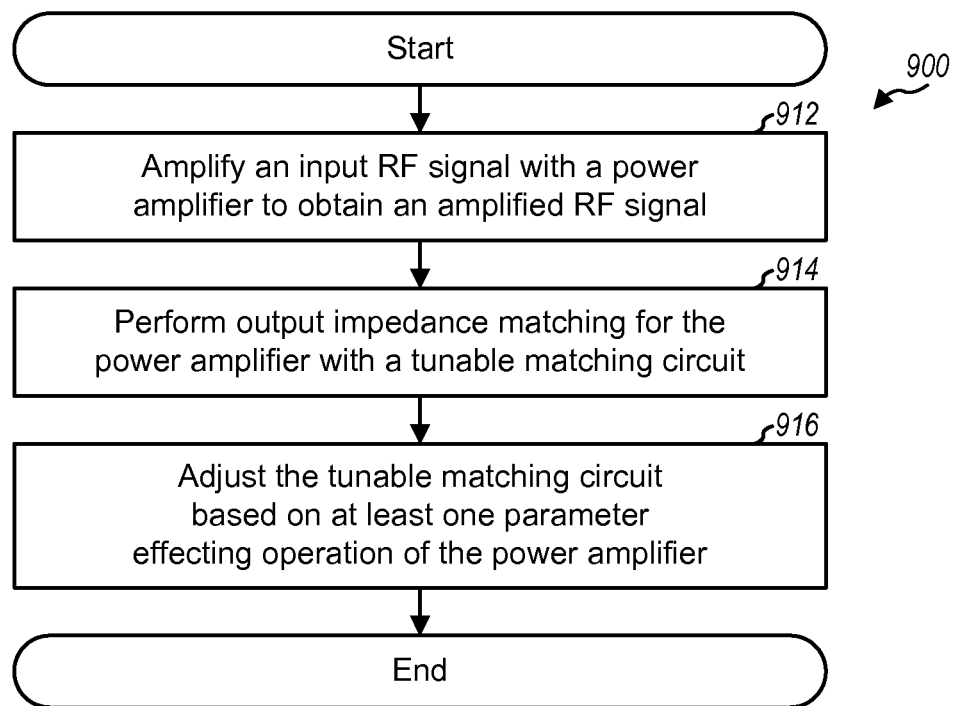


FIG. 8

**FIG. 9**

1

TUNABLE MATCHING CIRCUITS FOR POWER AMPLIFIERS

I. CLAIM OF PRIORITY UNDER 35 U.S.C. §119

The present Application for Patent claims priority to Provisional Application Ser. No. 61/183,877, entitled "TUNABLE MATCHING CIRCUITS FOR POWER AMPLIFIERS," filed Jun. 3, 2009, assigned to the assignee hereof, and expressly incorporated herein by reference.

BACKGROUND

I. Field

The present disclosure relates generally to electronics, and more specifically to matching circuits for power amplifiers.

II. Background

A wireless communication device typically includes a transmitter to support data transmission. The transmitter may have a power amplifier to amplify a radio frequency (RF) signal and provide high output power. The power amplifier may be designed to drive a particular load impedance (e.g., 50 Ohms) and to have the best possible efficiency at the maximum output power level. The power amplifier may operate over a wide range of output power levels, and the efficiency of the power amplifier typically decreases at lower output power levels. It may be desirable to improve the efficiency of the power amplifier at lower output power levels, which may be much more common than the maximum output power level.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 shows a block diagram of a wireless communication device.

FIG. 2 shows a block diagram of two power amplifiers and an output circuit.

FIG. 3 shows efficiency versus output power with tunable impedance matching.

FIGS. 4A and 4B show a tunable matching circuit with tunable series reactance.

FIGS. 5A and 5B show a tunable matching circuit with tunable shunt reactance.

FIGS. 6A and 6B show a tunable matching circuit with tunable series and shunt reactance.

FIGS. 7A and 7B show a two-stage tunable matching circuit.

FIG. 8 shows three tunable matching circuits for the output circuit.

FIG. 9 shows a process for amplifying a signal.

DETAILED DESCRIPTION

The word "exemplary" is used herein to mean "serving as an example, instance, or illustration." Any design described herein as "exemplary" is not necessarily to be construed as preferred or advantageous over other designs.

Tunable matching circuits that may improve the efficiency of power amplifiers are described herein. The tunable matching circuits may be used for various electronics devices such as wireless communication devices, cellular phones, personal digital assistants (PDAs), handheld devices, wireless modems, laptop computers, cordless phones, Bluetooth devices, consumer electronics devices, etc. For clarity, the use of the tunable matching circuits in a wireless communication device is described below.

FIG. 1 shows a simplified block diagram of an exemplary design of a wireless communication device 100. In this exem-

2

plary design, wireless device 100 includes one or more processors/controllers 110, a memory 112, and a transmitter 120. In general, wireless device 100 may include any number of transmitters and any number of receivers for any number of communication systems and any number of frequency bands.

In the exemplary design shown in FIG. 1, transmitter 120 includes N transmit signal paths, where N may be any integer value. The N transmit signal paths may be for different radio technologies, different frequency bands, etc. Each transmit signal path includes transmitter circuits 130 and a power amplifier (PA) 140. An output circuit 150 couples to all N power amplifiers 140a through 140n and also to K antennas 152a through 152k, where K may be any integer value. Output circuit 150 may perform impedance matching for power amplifiers 140 and may also route one or more RF signals from one or more power amplifiers 140 to one or more antennas 152.

Processor(s) 110 process data to be transmitted via one or more transmit signal paths and provide an analog output signal to each transmit signal path. For each transmit signal path, transmitter circuits 130 amplify, filter, and upconvert the analog output signal for that transmit signal path and provide an input RF signal. Power amplifier 140 amplifies the input RF signal to obtain the desired output power level and provides an amplified RF signal to output circuit 150. Output circuit 150 performs impedance matching and switching and provides an output RF signal to a selected antenna 152.

FIG. 1 shows an exemplary design of transmitter 120. In general, the conditioning of the signals in transmitter 120 may be performed by one or more stages of amplifier, filter, mixer, etc. All or a portion of transmitter 120 may be implemented on one or more analog integrated circuits (ICs), RF ICs (RFICs), mixed-signal ICs, etc.

Processor/controller(s) 110 may perform various functions for wireless device 100, e.g., processing for data to be transmitted. Processor/controller(s) 110 may also control the operation of various circuits within wireless device 100. Memory 112 may store program codes and data for processor/controller(s) 110. Processor/controller(s) 110 and memory 112 may be implemented on one or more application specific integrated circuits (ASICs) and/or other ICs.

FIG. 2 shows a block diagram of an exemplary design of output circuit 150 for a case with two power amplifiers 140a and 140b for two transmit signal paths. A first transmit signal path may be for Code Division Multiple Access (CDMA) and/or Wideband CDMA (WCDMA) for a first frequency band (Band 1). A second transmit signal path may be for CDMA/WCDMA for a second frequency band (Band 2). A third output for Global System for Mobile Communications (GSM) may be formed by combining the outputs of the first and second transmit signal paths. In general, any number of transmit signal paths may be used to support any number of radio technologies, any radio technology, and any number of frequency bands.

Power amplifier 140a amplifies a first input RF signal (Rfin1) and provides a first amplified RF signal. Within output circuit 150, a tunable matching circuit 210a is coupled to the output of power amplifier 140a and provides output impedance matching for power amplifier 140a. A switch 220a couples a first output RF signal (Rfout1) from tunable matching circuit 210a to either a first output for CDMA/WCDMA Band 1 or a tunable matching circuit 210c. A sensor 240a receives the first amplified RF signal from power amplifier 140a and the first output RF signal from tunable matching circuit 210a. Sensor 240a may measure the power, voltage, and/or current of one or both RF signals and may provide measurements to a control unit 230. The measurements from

3

sensor **240a** may be used to characterize the impedance of tunable matching circuit **210a** and/or the performance of the first transmit signal path. The measurements may be used to control/adjust tunable matching circuit **210a**.

Power amplifier **140b** amplifies a second input RF signal (RFin2) and provides a second amplified RF signal. Within output circuit **150**, a tunable matching circuit **210b** is coupled to the output of power amplifier **140b** and provides output impedance matching for power amplifier **140b**. A switch **220b** couples a second output RF signal (RFout2) from tunable matching circuit **210b** to either a second output for CDMA/WCDMA Band 2 or tunable matching circuit **210c**. A sensor **240b** receives the second amplified RF signal from power amplifier **140b** and the second output RF signal from tunable matching circuit **210b**. Sensor **240b** may measure the power, voltage, and/or current of one or both RF signals and may provide measurements to control unit **230**. The measurements from sensor **240b** may be used to characterize the impedance of tunable matching circuit **210b** and/or the performance of the second transmit signal path. The measurements may be used to control/adjust tunable matching circuit **210b**.

Control unit **230** may receive an envelope signal for each active transmit signal path, information indicative of an average output power level of each active transmit signal path, and/or information for other parameters (e.g., frequency band, operating mode, etc.) affecting the operation of power amplifiers **140a** and **140b**, e.g., from processor/controller(s) **110** in FIG. 1. An active transmit signal path is a transmit signal path selected for use and is operating. Control unit **230** may also receive measurements (e.g., for power, voltage, current, etc.) from sensor **240** for each active transmit signal path. Control unit **230** may also receive measurements (e.g., for power supply voltage, temperature, etc.) from sensor(s) **250**. Control unit **230** may generate at least one control (Control1 or Control2) for each tunable matching circuit **210** based on the received inputs to achieve good performance, e.g., to improve the efficiency of each active power amplifier **140**. Control unit **230** may also provide measurements (e.g., for power, voltage, current, etc.) to processor/controller(s) **110**, which may control the operation of tunable matching circuits **210**, power amplifiers **140**, etc.

A power amplifier may have a certain output impedance (Z_{pa}) and may be designed to drive a particular load impedance (Z_o). For example, the output impedance of the power amplifier may be approximately 4 Ohms whereas the load impedance may be 50 Ohms. A matching circuit may be used to match the PA output impedance to the load impedance in order to achieve good performance. The matching circuit may be a fixed matching circuit that may be designed to provide good performance (e.g., high PA efficiency) at the maximum output power level. However, this fixed matching circuit may provide sub-optimal performance (e.g., lower PA efficiency) at lower output power levels. The lower output power levels may occur much more frequently than the maximum output power level.

In an aspect, each tunable matching circuit **210** may provide tunable impedance matching for an associated power amplifier **140**. In a first exemplary design, the tunable impedance matching may be dynamically varied based on an envelope signal indicative of the envelope of the amplified RF signal from power amplifier **140**. In a second exemplary design, the tunable impedance matching may be varied based on an average output power level of the amplified RF signal from power amplifier **140**. The first exemplary design may allow the tunable impedance matching to be varied at a relatively fast rate, e.g., on the order of microseconds (μs). The

4

second exemplary design may allow the tunable impedance matching to be varied at a slower rate, e.g., on the order of milliseconds (ms) or slower. The envelope signal or the average output power level may be provided by processor(s) **110** based on the operating state of wireless device **100**. In a third exemplary design, sensor **240** may measure the power, voltage, and/or current of the amplified RF signal and/or the output RF signal for tunable matching circuit **210**. The measurements may be used to vary the tunable impedance matching. The tunable impedance matching may also be varied in other manners.

FIG. 3 shows plots of efficiency versus output power level (P_{out}) for a power amplifier with tunable impedance matching. The horizontal axis shows P_{out} , which is given in units of dBm. The vertical axis shows efficiency, which is given in percent (%). A plot **310** shows efficiency versus P_{out} for a nominal output impedance matching, which may be designed for the maximum output power level. Plots **312**, **314**, **316**, **318** and **320** show efficiency versus P_{out} for five different impedance matching settings. Each impedance matching setting may correspond to a specific value for each configurable component (e.g., each variable capacitor) in a tunable matching circuit.

As shown in FIG. 3, different impedance matching settings may provide different efficiencies at different output power levels. For example, the impedance matching setting corresponding to plot **320** may provide better efficiency between 21 and 26 dBm but may be able to provide a peak output power level of 26 dBm. Different impedance matching settings may be used for different ranges of output power levels to maximize efficiency. For example, the setting corresponding to plot **320** may be used for 26 dBm or lower, the setting corresponding to plot **318** may be used between 26 dBm and 27.5 dBm, the setting corresponding to plot **316** may be used between 27.5 dBm and 29 dBm, the setting corresponding to plot **314** may be used between 29 dBm and 31 dBm, and the setting corresponding to plot **310** or **312** may be used above 31 dBm.

Tunable matching circuits **210a**, **210b** and **210c** in FIG. 2 may be implemented in various manners. Some exemplary designs of tunable matching circuits **210** are described below.

FIG. 4A shows an exemplary design of a single-stage tunable matching circuit **210u** with tunable series reactance. Tunable matching circuit **210u** may be used for any one of tunable matching circuits **210a**, **210b** and **210c** in FIG. 2. In the exemplary design shown in FIG. 4A, tunable matching circuit **210u** includes an inductor **410** and a variable capacitor **420** coupled in parallel and between the input (node A) and the output (node B) of tunable matching circuit **210u**. A shunt capacitor **430** is coupled between node B and circuit ground. Capacitor **420** has a variable capacitance of C_{var} , which may be varied within a range of C_{min} to C_{max} , or $C_{min} \leq C_{var} \leq C_{max}$. Inductor **410** has a fixed inductance of L , and capacitor **430** has a fixed capacitance of C_{sh} . The inductance L and the capacitances C_{sh} and C_{min} may be selected to obtain the nominal output impedance matching at the maximum output power level, e.g., to obtain plot **310** in FIG. 3. Different impedance matching settings may be obtained with different values of C_{var} .

Series capacitor **420** may have a tendency to increase the inductance of inductor **410**, which may be desirable. Capacitor **420** and inductor **410** also form a resonator with a resonant frequency determined by the capacitance of capacitor **420** and the inductance of inductor **410**. The resonator has high impedance at the resonant frequency and may be used as a trap to attenuate an undesired harmonic of the amplified RF signal. For example, capacitor **420** may be varied such that the

5

resonant frequency is at a second harmonic or a third harmonic of the amplified RF signal.

FIG. 4B shows an exemplary design of tunable matching circuit **210u** in FIG. 4A using switchable capacitors. In the exemplary design shown in FIG. 4B, variable capacitor **420** is implemented with four capacitors **422a**, **422b**, **422c** and **422d** coupled in parallel. Capacitor **422a** is a fixed capacitor that is always selected, and capacitors **422b**, **422c** and **422d** are switchable capacitors that may each be selected or deselected.

Capacitor **422a** is coupled directly between nodes A and B. Capacitor **422b** is coupled in series with multiple (e.g., five) metal oxide semiconductor (MOS) transistors **424b**, and the combination is coupled between nodes A and B. MOS transistors **424b** operate as a switch that can connect or disconnect capacitor **422b** from node B. Similarly, capacitor **422c** is coupled in series with multiple (e.g., five) MOS transistors **424c**, and the combination is coupled between nodes A and B. Capacitor **422d** is coupled in series with multiple (e.g., five) MOS transistors **424d**, and the combination is coupled between nodes A and B. The gates of MOS transistors **424b** receive a Ctrl11 control signal via resistors **426b**, the gates of MOS transistors **424c** receive a Ctrl12 control signal via resistors **426c**, and the gates of MOS transistors **424d** receive a Ctrl13 control signal via resistors **426d**. The Ctrl11, Ctrl12 and Ctrl13 control signals may be part of the Control1 or Control2 provided by control unit **230** in FIG. 2.

As shown in FIG. 4B, multiple MOS transistors **424** may be stacked together for each switch, so that only a fraction of the output RF signal is applied across each MOS transistor. MOS transistors **424** may have a small operating voltage in comparison to the output RF signal swing. The use of multiple MOS transistors **424** stacked together may improve reliability. The number of MOS transistors to stack together may be selected based on the rated operating voltage of the MOS transistors and the maximum output power level of the output RF signal.

The exemplary design shown in FIG. 4B uses binary weighting. Capacitor **422a** may have a capacitance of C, capacitor **422b** may also have a capacitance of C, capacitor **422c** may have a capacitance of 2 C, and capacitor **422d** may have a capacitance of 4 C. C may be one picoFarad (pF) or some other suitable capacitance value, which may be selected based on the frequency band of operation. In another exemplary design, thermometer decoding may be used, and capacitors **422a** through **422d** may have the same capacitance.

In general, any number of fixed and switchable capacitors may be used to form variable capacitor **420**. Furthermore, each fixed or switchable capacitor may have any suitable capacitance value. Different impedance matching settings may be obtained with different combinations of switchable capacitors being selected. For example, eight different impedance matching settings ranging from C to 8 C may be obtained with eight different switching states for the three switches for capacitors **422b**, **422c** and **422d**.

FIG. 5A shows an exemplary design of a single-stage tunable matching circuit **210v** with tunable shunt reactance. Tunable matching circuit **210v** may also be used for any one of tunable matching circuits **210a**, **210b** and **210c** in FIG. 2. In the exemplary design shown in FIG. 5A, tunable matching circuit **210v** includes inductor **410** coupled between the input (node A) and the output (node B) of tunable matching circuit **210v**. A variable shunt capacitor **440** is coupled between node B and circuit ground. Inductor **410** has a fixed inductance of L, and capacitor **440** has a variable capacitance of Cvar. Different impedance matching settings may be obtained with different values of Cvar.

6

FIG. 5B shows an exemplary design of tunable matching circuit **210v** in FIG. 5A using switchable capacitors. In the exemplary design shown in FIG. 5B, variable capacitor **440** is implemented with four capacitors **442a**, **442b**, **442c** and **442d** coupled in parallel. Capacitor **442a** is a fixed capacitor that is always selected, and capacitors **442b**, **442c** and **442d** are switchable capacitors that may each be selected or deselected.

Capacitor **442a** is coupled directly between node B and circuit ground. Capacitor **442b** is coupled in series with multiple (e.g., five) MOS transistors **444b**, capacitor **442c** is coupled in series with multiple MOS transistors **444c**, and capacitor **442d** is coupled in series with multiple MOS transistors **444d**. The three series combinations of capacitor **442** and MOS transistors **444** are coupled between node B and circuit ground. The gates of MOS transistors **444b** receive a Ctrl21 control signal via resistors **446b**, the gates of MOS transistors **444c** receive a Ctrl22 control signal via resistors **446c**, and the gates of MOS transistors **444d** receive a Ctrl23 control signal via resistors **446d**. The Ctrl21, Ctrl22 and Ctrl23 control signals may be part of the Control1 or Control2 provided by control unit **230** in FIG. 2.

For binary weighting, capacitor **442a** may have a capacitance of C, capacitor **442b** may also have a capacitance of C, capacitor **442c** may have a capacitance of 2 C, and capacitor **442d** may have a capacitance of 4 C. For thermometer decoding, capacitors **442a** through **442d** may have the same capacitance. In general, any number of fixed and switchable capacitors may be used to form variable capacitor **440**, and each fixed or switchable capacitor may have any suitable capacitance value.

FIG. 6A shows an exemplary design of a single-stage tunable matching circuit **210w** with tunable series and shunt reactance. Tunable matching circuit **210w** may also be used for any one of tunable matching circuits **210a**, **210b** and **210c** in FIG. 2. In the exemplary design shown in FIG. 6A, tunable matching circuit **210w** includes inductor **410** and variable capacitor **420** coupled in parallel and between the input (node A) and the output (node B) of tunable matching circuit **210w**. Variable shunt capacitor **440** is coupled between node B and circuit ground. Inductor **410** has a fixed inductance of L, capacitor **420** has a variable capacitance of Cvar1, and capacitor **440** has a variable capacitance of Cvar2. Different impedance matching settings may be obtained with different combination of values for Cvar1 and Cvar2.

FIG. 6B shows an exemplary design of tunable matching circuit **210w** in FIG. 6A using switchable capacitors. In the exemplary design shown in FIG. 6B, variable series capacitor **420** is implemented with four capacitors **422a**, **422b**, **422c** and **422d** and MOS transistors **424a**, **424b**, **424c** and **424d**, which are coupled as described above for FIG. 4B. Variable shunt capacitor **440** is implemented with four capacitors **442a**, **442b**, **442c** and **442d** and MOS transistors **444a**, **444b**, **444c** and **444d**, which are coupled as described above for FIG. 5B. Capacitors **422b**, **422c** and **422d** may be selected or deselected by the Ctrl11, Ctrl12 and Ctrl13 control signals, respectively. Capacitors **442b**, **442c** and **442d** may be selected or deselected by the Ctrl21, Ctrl22 and Ctrl23 control signals, respectively. In general, any number of fixed and switchable capacitors may be used to implement each of variable capacitors **420** and **440**. Each fixed or switchable capacitor may have any suitable capacitance value.

FIG. 7A shows an exemplary design of a two-stage tunable matching circuit **210x** with tunable series and shunt reactance. Tunable matching circuit **210x** may also be used for any one of tunable matching circuits **210a**, **210b** and **210c** in FIG. 2. In the exemplary design shown in FIG. 7A, tunable matching circuit **210x** includes a first stage comprising inductor

7

410, variable series capacitor 420, and variable shunt capacitor 440, which are coupled between nodes A and B as described above for FIG. 6A. Tunable matching circuit 210x further includes a second stage comprising an inductor 450, a variable series capacitor 460, and a variable shunt capacitor 470, which are coupled between nodes B and D in similar manner as the first stage. Different impedance matching settings may be obtained with different combinations of values for Cvar1, Cvar2, Cvar3 and Cvar4 for variable capacitors 420, 440, 460 and 470, respectively. Two stages may provide more degree of freedom to tune the impedance matching.

FIG. 7B shows an exemplary design of tunable matching circuit 210x in FIG. 7A using switchable capacitors. In the exemplary design shown in FIG. 7B, variable series capacitor 420 is implemented with capacitors 422a through 422d and MOS transistors 424a through 424d, which are coupled as described above for FIG. 4B. Variable shunt capacitor 440 is implemented with capacitors 442a through 442d and MOS transistors 444a through 444d, which are coupled as described above for FIG. 5B. Variable series capacitor 460 is implemented with capacitors 462a through 462d and MOS transistors 464a through 464d, which are coupled in similar manner as capacitors 422 and MOS transistors 424. Variable shunt capacitor 470 is implemented with capacitors 472a through 472d and MOS transistors 474a through 474d, which are coupled in similar manner as capacitors 442 and MOS transistors 444. In general, any number of fixed and switchable capacitors may be used to implement each of variable capacitors 420, 440, 460 and 470. Furthermore, each fixed or switchable capacitor may have any suitable capacitance value.

FIG. 8 shows an exemplary design of tunable matching circuits 210a, 210b and 210c in FIG. 2. In this exemplary design, each tunable matching circuit 210 is implemented with inductor 410, variable series capacitor 420, and variable shunt capacitor 440, which are coupled as described above for FIG. 6A. Tunable matching circuit 210a matches the output impedance Zpa1 of power amplifier 140a to the load impedance Zo. Similarly, tunable matching circuit 210b matches the output impedance Zpa2 of power amplifier 140b to the load impedance Zo.

Switches 220a and 220b may be configured to couple the outputs of tunable matching circuits 210a and 210b to the input of tunable matching circuit 210c. In this case, tunable matching circuit 210c would observe an input impedance of Zo/2 and would match Zo/2 to the load impedance Zo. Tunable matching circuits 210a, 210b and 210c may have the same topology. However, different values of inductor 410 and/or capacitors 420 and 440 may be used for different tunable matching circuits 210a, 210b and 210c.

In the exemplary designs described above, one or more switchable capacitors may be used to implement a variable capacitor. In another exemplary design, one or more varactors may be used to implement a variable capacitor. A varactor may have a capacitance that may be varied with a control voltage. A varactor may be implemented with a semiconductor device, a micro-electro-mechanical system (MEMS) device, etc.

Tunable matching circuits 210a, 210b and 210c may be adjusted based on various parameters. In an exemplary design, a given tunable matching circuit 210 may be adjusted based on an envelope signal for an associated power amplifier 140. This exemplary design may be used to track variations in the envelop of an output RF signal, e.g., due to a high peak-to-average power ratio (PAPR). For example, the peak output power level may be about 4 dB higher than the average output

8

power level for a CDMA signal. The tuning may attempt to track changes in the output power level due to PAPR.

In another exemplary design, tunable matching circuit 210 may be adjusted based on an average output power level of the associated power amplifier 140. This exemplary design may be especially suitable for RF signals with a constant envelope, such as a GSM signal.

In yet another exemplary design, tunable matching circuit 210 may be adjusted based on measurements for power, voltage and/or current from associated sensor 240. The measurements may be used to detect impedance mismatch and to adjust tunable matching circuit 210 accordingly.

In yet another exemplary design, tunable matching circuit 210 may be adjusted based on a Vdd power supply voltage for associated power amplifier 140. The power supply voltage may be provided by a battery, a DC switching circuit, etc. Power amplifier 140 may operate over a range of power supply voltages. The efficiency of power amplifier 140 typically decreases with higher power supply voltage. It may be desirable to improve the efficiency of power amplifier 140 at higher power supply voltage. It may also be desirable to operate power amplifier 140 at lower power supply voltage. This may support battery technologies that can supply power at lower voltage and thus provide longer operating time. In an exemplary design, different sets of performance plots may be obtained for different power supply voltages for power amplifier 140. Each set of performance plots may be similar to the set of plots shown in FIG. 3 and may be for one specific power supply voltage. Different impedance matching settings may be used for different power supply voltages to achieve good performance, e.g., better PA efficiency and/or better PA performance. For example, the power supply voltage for power amplifier 140 may be measured, and the set of performance plots corresponding to the measured power supply voltage may be used. Different impedance matching settings may then be selected based on this set of performance plots. In another exemplary design, a set of performance plots may be obtained for power amplifier 140 for different power supply voltages with a specific impedance matching setting. One performance plot may be selected for use based on the measured power supply voltage.

Adjusting tunable matching circuit 210 based on the power supply voltage may improve PA efficiency and may also support operation of power amplifier 140 at a lower power supply voltage.

In yet another exemplary design, tunable matching circuit 210 may be adjusted based on temperature observed by associated power amplifier 140. A set of performance plots may be obtained for different temperatures for power amplifier 140. Different impedance matching settings may be used for different temperatures to achieve good performance. For example, the temperature of power amplifier 140 may be sensed, and the set of performance plots corresponding to the sensed temperature may be used. Different impedance matching settings may then be selected based on this set of performance plots.

In yet another exemplary design, tunable matching circuit 210 may be adjusted based on IC process variations. A set of performance plots may be obtained for different IC process corners. Different impedance matching settings may be used for different IC process corners to achieve good performance.

In yet another exemplary design, tunable matching circuit 210 may be adjusted based on frequency band of operation. Different sets of performance plots may be obtained for power amplifier 140 for different frequency bands. The set of performance plots corresponding to a selected frequency band may be used.

In yet another exemplary design, tunable matching circuit **210** may be adjusted based on operating mode. Different sets of performance plots may be obtained for power amplifier **140** for different operating modes, e.g., a linear mode, a saturated mode, etc. The set of performance plots corresponding to the current operating mode of power amplifier **140** may be used.

In yet another exemplary design, tunable matching circuit **210** may be adjusted based on the load. A set of performance plots may be obtained for different load values. Different impedance matching settings may be used for different load values to achieve good performance. Tunable matching circuit **210** may also be adjusted based on other parameters such as harmonics rejection, etc.

Tunable matching circuit **210** may also be adjusted in other manners, e.g., based on other parameters that may affect the operation or performance of power amplifier **140**. In an exemplary design, a look-up table may store different impedance matching settings for different parameter values. A suitable impedance matching setting may be obtained by applying the current parameter values to the look-up table.

In an exemplary design, an apparatus may comprise a power amplifier (power amplifier **140a** in FIG. 2 or 8) and a tunable matching circuit (e.g., tunable matching circuit **210a**). The power amplifier may amplify an input RF signal and provide an amplified RF signal. The tunable matching circuit may provide output impedance matching for the power amplifier, may receive the amplified RF signal and provide an output RF signal, and may be tunable based on at least one parameter effecting the operation of the power amplifier.

In an exemplary design, the tunable matching circuit may comprise a variable capacitor (e.g., capacitor **420** in FIG. 4A or 6A) coupled in series between the input and output of the tunable matching circuit. Alternatively or additionally, the tunable matching circuit may comprise a variable capacitor (e.g., capacitor **440** in FIG. 5A or 6A) coupled between the output of the tunable matching circuit and circuit ground. Each variable capacitor may be tunable based on the at least one parameter. In another exemplary design, the tunable matching circuit may comprise multiple stages (e.g., as shown in FIGS. 7A and 7B). Each stage may comprise at least one variable capacitor that may be tunable based on the at least one parameter.

The apparatus may further comprise a control unit that may receive information indicative of the at least one parameter and may generate at least one control for the tunable matching circuit based on the received information. The apparatus may further comprise a sensor that may measure the amplified RF signal and/or the output RF signal. The control unit may receive measurements from the sensor and may adjust the tunable matching circuit based on the measurements.

In an exemplary design, the at least one parameter may comprise an envelope signal for the amplified RF signal. The tunable matching circuit may be adjusted based on the envelope signal. In another exemplary design, the parameter(s) may comprise an average output power level of the output RF signal. The tunable matching circuit may be adjusted based on the average output power level. In yet another exemplary design, the parameter(s) may comprise a power supply voltage for the power amplifier. The tunable matching circuit may be adjusted based on the power supply voltage. In yet another exemplary design, the parameter(s) may comprise IC process variations. The tunable matching circuit may be adjusted based on a detected IC process corner for the power amplifier. The tunable matching circuit may also be adjusted based on other parameters.

The apparatus may further comprise a second power amplifier (e.g., power amplifier **140b** in FIG. 2 or 8) and a second tunable matching circuit (e.g., tunable matching circuit **210b**). The second power amplifier may amplify a second input RF signal and provide a second amplified RF signal. The second tunable matching circuit may provide output impedance matching for the second power amplifier, may receive the second amplified RF signal and provide a second output RF signal, and may be tunable based on at least one second parameter effecting the operation of the second power amplifier. The apparatus may further comprise a third tunable matching circuit (e.g., tunable matching circuit **210c**) that may receive the first and second output RF signals and provide a third output RF signal.

In an exemplary design, a wireless device may comprise a power amplifier, a tunable matching circuit, and a control unit, e.g., as shown in FIG. 2. The power amplifier may amplify an input RF signal and provide an amplified RF signal. The tunable matching circuit may provide output impedance matching for the power amplifier and may receive the amplified RF signal and provide an output RF signal. The control unit may generate a control to adjust the tunable matching circuit based on at least one parameter effecting the operation of the power amplifier. The tunable matching circuit may include a variable capacitor coupled in series between the input and output of the tunable matching circuit and/or a variable capacitor coupled between the output and circuit ground. Each variable capacitor may be tunable based on the control from the control unit. The wireless device may further comprise a sensor that may measure the amplified RF signal and/or the output RF signal and may generate the control for the tunable matching circuit based on measurements from the sensor.

FIG. 9 shows a design of a process **900** for amplifying a signal. An input RF signal may be amplified with a power amplifier to obtain an amplified RF signal (block **912**). Output impedance matching may be performed for the power amplifier with a tunable matching circuit (block **914**). The tunable matching circuit may be adjusted based on at least one parameter effecting the operation of the power amplifier (block **916**). For example, the tunable matching circuit may be adjusted based on an envelope signal for the power amplifier, an average output power level for the power amplifier, a power supply voltage for the power amplifier, etc. In an exemplary design, a variable capacitor in the tunable matching circuit may be adjusted based on a control generated based on the parameter(s). In an exemplary design, the amplified RF signal and/or an output RF signal may be measured, and the tunable matching circuit may be adjusted based on measurements of the amplified RF signal and/or the output RF signal.

The tunable matching circuits described herein may be implemented on an IC, an analog IC, an RFIC, a mixed-signal IC, an ASIC, a printed circuit board (PCB), an electronics device, etc. The tunable matching circuits may also be fabricated with various IC process technologies such as complementary metal oxide semiconductor (CMOS), N-channel MOS (NMOS), P-channel MOS (PMOS), bipolar junction transistor (BJT), bipolar-CMOS (BiCMOS), silicon germanium (SiGe), gallium arsenide (GaAs), etc.

An apparatus implementing the tunable matching circuits described herein may be a stand-alone device or may be part of a larger device. A device may be (i) a stand-alone IC, (ii) a set of one or more ICs that may include memory ICs for storing data and/or instructions, (iii) an RFIC such as an RF receiver (RFR) or an RF transmitter/receiver (RTR), (iv) an ASIC such as a mobile station modem (MSM), (v) a module

11

that may be embedded within other devices, (vi) a receiver, cellular phone, wireless device, handset, or mobile unit, (vii) etc.

In one or more exemplary designs, the functions described may be implemented in hardware, software, firmware, or any combination thereof. If implemented in software, the functions may be stored on or transmitted over as one or more instructions or code on a computer-readable medium. Computer-readable media includes both computer storage media and communication media including any medium that facilitates transfer of a computer program from one place to another. A storage media may be any available media that can be accessed by a computer. By way of example, and not limitation, such computer-readable media can comprise RAM, ROM, EEPROM, CD-ROM or other optical disk storage, magnetic disk storage or other magnetic storage devices, or any other medium that can be used to carry or store desired program code in the form of instructions or data structures and that can be accessed by a computer. Also, any connection is properly termed a computer-readable medium. For example, if the software is transmitted from a website, server, or other remote source using a coaxial cable, fiber optic cable, twisted pair, digital subscriber line (DSL), or wireless technologies such as infrared, radio, and microwave, then the coaxial cable, fiber optic cable, twisted pair, DSL, or wireless technologies such as infrared, radio, and microwave are included in the definition of medium. Disk and disc, as used herein, includes compact disc (CD), laser disc, optical disc, digital versatile disc (DVD), floppy disk and blu-ray disc where disks usually reproduce data magnetically, while discs reproduce data optically with lasers. Combinations of the above should also be included within the scope of computer-readable media.

The previous description of the disclosure is provided to enable any person skilled in the art to make or use the disclosure. Various modifications to the disclosure will be readily apparent to those skilled in the art, and the generic principles defined herein may be applied to other variations without departing from the scope of the disclosure. Thus, the disclosure is not intended to be limited to the examples and designs described herein but is to be accorded the widest scope consistent with the principles and novel features disclosed herein.

What is claimed is:

1. An apparatus comprising:
 - a power amplifier amplifying an input radio frequency (RF) signal and providing an amplified RF signal;
 - a tunable matching circuit coupled to the power amplifier and providing output impedance matching for the power amplifier, the tunable matching circuit receiving the amplified RF signal and providing an output RF signal, the tunable matching circuit being adaptively tunable to a setting based on at least one parameter affecting operation of the power amplifier, the setting causing a power efficiency of the power amplifier to be greater than a power efficiency at a different setting; and
 - at least one sensor coupled to each of an output of the power amplifier and an output of the tunable matching circuit and configured to measure at least one property of each of the amplified RF signal and the output RF signal.
2. The apparatus of claim 1, the tunable matching circuit comprising
 - a variable capacitor coupled in series between an input and an output of the tunable matching circuit, the variable capacitor being tunable based on the at least one parameter.
3. The apparatus of claim 1, the tunable matching circuit comprising

12

a variable capacitor coupled between an output of the tunable matching circuit and circuit ground, the variable capacitor being tunable based on the at least one parameter.

4. The apparatus of claim 2, the tunable matching circuit further comprising

a second variable capacitor coupled between the output of the tunable matching circuit and circuit ground, the second variable capacitor being tunable generated based on the at least one parameter.

5. The apparatus of claim 1, the tunable matching circuit comprising multiple stages, each stage comprising at least one variable capacitor tunable based on the at least one parameter.

6. The apparatus of claim 1, further comprising:

a control unit receiving information indicative of the at least one parameter and generating at least one control for the tunable matching circuit based on the received information.

7. The apparatus of claim 1, the at least one parameter comprising an envelope signal for the amplified RF signal, and the tunable matching circuit being adjusted based on the envelope signal.

8. The apparatus of claim 1, the at least one parameter comprising an average output power level of the output RF signal, and the tunable matching circuit being adjusted based on the average output power level.

9. The apparatus of claim 1, the at least one parameter comprising a power supply voltage for the power amplifier, and the tunable matching circuit being adjusted based on the power supply voltage.

10. The apparatus of claim 1, the at least one parameter comprising integrated circuit (IC) process variations, and the tunable matching circuit being adjusted based on a detected IC process corner for the power amplifier.

11. The apparatus of claim 1, the at least one parameter comprising temperature, frequency band, load, harmonic rejection, operating mode of the power amplifier, or a combination thereof.

12. The apparatus of claim 1, further comprising:

a second power amplifier amplifying a second input RF signal and providing a second amplified RF signal; and a second tunable matching circuit coupled to the second power amplifier and providing output impedance matching for the second power amplifier, the second tunable matching circuit receiving the second amplified RF signal and providing a second output RF signal, the second tunable matching circuit being tunable based on at least one second parameter affecting operation of the second power amplifier.

13. The apparatus of claim 12, further comprising:

a third tunable matching circuit coupled to the first and second tunable matching circuits, the third tunable matching circuit receiving the first and second output RF signals and providing a third output RF signal.

14. The apparatus of claim 1, further comprising:

a sensor coupled to the tunable matching circuit and measuring the amplified RF signal, or the output RF signal, or both; and

a control unit receiving measurements from the sensor and adjusting the tunable matching circuit based on the measurements.

15. A wireless device comprising:

a power amplifier amplifying an input radio frequency (RF) signal and providing an amplified RF signal;

a tunable matching circuit coupled to the power amplifier and providing output impedance matching for the power

13

amplifier, the tunable matching circuit receiving the amplified RF signal and providing an output RF signal; at least one sensor coupled to each of an output of the power amplifier and an output of the tunable matching circuit and configured to measure at least one property of each of the amplified RF signal and the output RF signal; and a control unit generating a control to adjust the tunable matching circuit to a setting based on at least one parameter affecting operation of the power amplifier, the setting causing a power efficiency of the power amplifier to be greater than a power efficiency at a different setting.

16. The wireless device of claim 15, the tunable matching circuit comprising

- a variable capacitor coupled in series between an input and an output of the tunable matching circuit, the variable capacitor being tunable based on the control from the control unit.

17. The wireless device of claim 15, further comprising:

- a sensor coupled to the tunable matching circuit and measuring the amplified RF signal, or the output RF signal, or both, the control unit generating the control for the tunable matching circuit based on measurements from the sensor.

18. A method of performing signal amplification, comprising:

- amplifying an input radio frequency (RF) signal with a power amplifier to obtain an amplified RF signal;
- performing output impedance matching for the power amplifier with a tunable matching circuit;
- sensing at least one property of each of the amplifier RF signal and an output of the tunable matching circuit; and
- adaptively adjusting the tunable matching circuit to a setting based on at least one parameter affecting operation of the power amplifier, the setting causing a power efficiency of the power amplifier to be greater than a power efficiency at a different setting.

14

19. The method of claim 18, the adjusting the tunable matching circuit comprising adjusting the tunable matching circuit based on an envelope signal for the power amplifier, an average output power level of the power amplifier, a power supply voltage for the power amplifier, or any combination thereof.

20. The method of claim 18, the adjusting the tunable matching circuit comprising

- measuring the amplified RF signal, or an output RF signal from the tunable matching circuit, or both, and
- adjusting the tunable matching circuit based on measurements of the amplified RF signal, or the output RF signal, or both.

21. The method of claim 18, the adjusting the tunable matching circuit comprising

- generating a control based on the at least one parameter, and
- adjusting a variable capacitor in the tunable matching circuit based on the control.

22. An apparatus comprising:

- means for amplifying an input radio frequency (RF) signal to obtain an amplified RF signal;
- means for matching an output impedance of the means for amplifying;
- means for sensing at least one property of each of the amplifier RF signal and an output of the tunable matching circuit; and
- means for adaptively adjusting the means for matching the output impedance to a setting based on at least one parameter affecting operation of the means for amplifying, the setting causing a power efficiency of the means for amplifying to be greater than a power efficiency at a different setting.

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